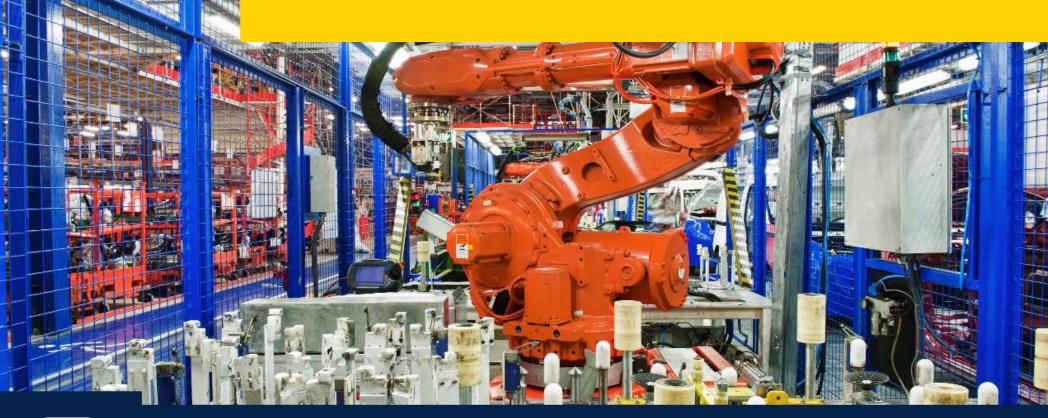




AMS & P&D
Growth Products
introductions as @Q1'24

EMEA Product Marketing

Analog & Sensors









VL53**L4ED** extended temperature capability

Time-of-Flight high accuracy proximity sensor with extended temperature capability

Highlights

VL53L4ED

- Single-zone ToF
- High performance proximity sensor
- · Short distance linearity down to 1mm
- From 0 to 1300mm with full field-of-view
- 18° diagonal FoV
- Extended effective temperature range of -40°C to 105°C
- Up to 800 mm ranging under 5 kLux
- Fast ranging frequency up to 100 Hz
- 4.4 x 2.4 x 1 mm size
- Pin-to-pin compatible with VL53L4CD





Tools

Evaluation Kits:

X-NUCLEO-53L4A3 P-NUCLEO-53L4A3 SATEL-VL53L4ED

Software:

Ultra-Light Driver
GUI for X-Nucleo board
Linux Driver
X-Cube example

Documentation

Datasheet
User manual & AN



Applications

Typical use-cases

- Industrial automation & Security systems
- Touchless button for Industrial tools
- Industrial manufacture assistance
- Liquid level monitoring (container, tanks, etc).

Applications









Tank

Industrial tools

Smart storage

Logistics & Industrial





What is your VL53L4 product?

Which ToF sensors should you choose from our VL53L4 family?

distance Linearity



Time-of-flight high accuracy proximity sensor with excellent short distance linearity

Single-zone VL53L4CD Package size :

4.4 x 2.4 x 1 mm

FoV: 18°

Distance measurement : up to 1.3 meters

Ranging under ambient light (5 klux): 80cm

Close distance linearity: >0.1cm

Typical power Consumption: 22mA

down to 55 μA with ultra-low power mode

Time-of-Flight sensor with extended range measurement

Single-zone Package size :

4.4 x 2.4 x 1 mm

FoV: 18°

Distance measurement : up to 6 meters

Multi-object

Ranging under ambient light (5 klux): 180cm

Long ranging

distance

Close distance linearity: >1cm

Typical power Consumption: 19mA



Extended Temperature range -40°C to 105°C

Time-of-Flight high accuracy proximity sensor with extended temperature capability

Single-zone **Distance measurement :** up to 1.3 meters

Package size : Ranging under ambient light (5 klux): 80cm

4.4 x 2.4 x 1 mm Close distance linearity: >0.1cm

FoV: 18° Typical power Consumption: 22mA

ST Restricted









TSC2020

100V precision bidirectional current sense amplifier

Flexibility

- Bidirectional current measurement
- High side or low side configuration possible
- Supply voltage range: 2.7V. to 5.5 V

High Performance

- Offset voltage: ± 150µV max.
- Offset drift: 0.5 µV/°C max.
- High common-mode rejection: 100dB min.
- Internal fixed gain 20 V/V
 - Gain error: 0.3% max.
 - Gain drift: 3.5 ppm/°C max.
 - Gain x50 and x100 in coming quarters
- Bandwidth: typ. 700 kHz

Robustness

- -4 to 100 V operating voltage on inputs
- Enhanced PWM rejection
- 2 kV HBM ESD tolerance
- Extended temperature range : -40 °C to +125 °C
- AEC-Q101 qualified: TSC2020IY







Applications

- · 48V systems
- Motor control
- Lighting
- Data Centres
- Automotive

ST Competitive Edge

- · Wide common mode voltage
- · Bidirectional sensing
- Integrated solution
- · Embedded EMI filters
- High accuracy

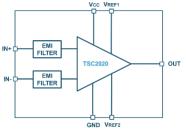
Competition:

- TI: INA240
- ADI: AD8418

Product Saletype

- TSC2020IDT/IST, DCPL 0.9756 Euros
- TSC2020IYDT/YIST, DCPL 1.1707 Euros





ST Restricted





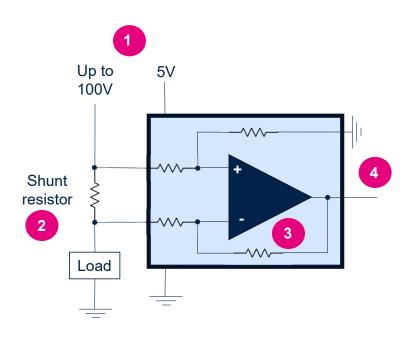






TSC2020 vs discrete

Discrete solution versus a dedicated current sense amplifier





Independent voltages

Power rail voltage can be higher vs. supply voltage



Precision current sense with low offset allows smaller shunt resistor and less power dissipation

TSC2020 is a bidirectional current sense amplifier, replacing 2 discrete op amps (for 2 directions) + all resistors



High accuracy and matched resistors for superior gain performance



OUT can be connected to a low voltage ADC or MCU











TSC2020

100V precision bidirectional current sense amplifier

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Robustness

life.augmented

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- Enhanced PWM rejection
- 2 kV HBM ESD tolerance
- Extended temperature range : -40 °C to +125 °C
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Mini SO8

Applications

- · 48V systems
- Motor control
- Lighting
- Data Centres
- Automotive

ST Competitive Edge

- · Wide common mode voltage
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- Integrated solution
- · Embedded EMI filters
- High accuracy

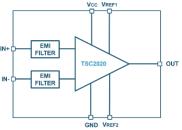
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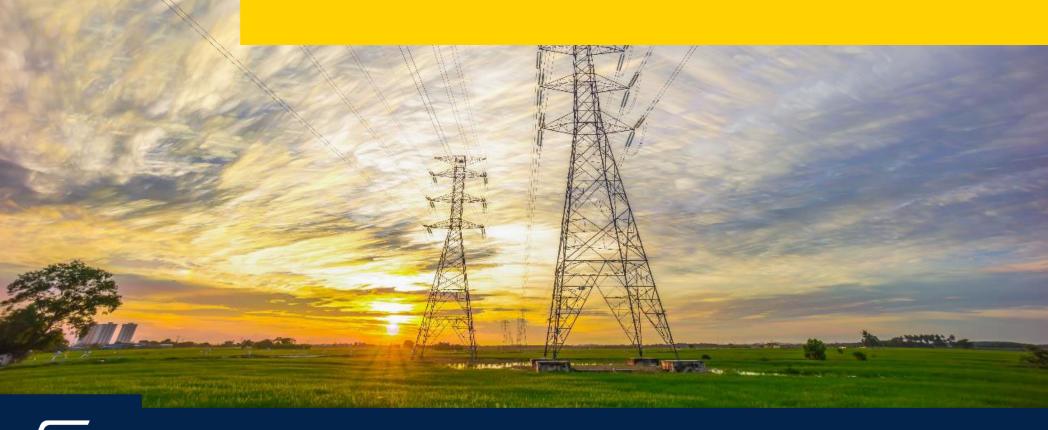
- TSC2020IDT/IST, DCPL 0.9756 Euros
- TSC2020IYDT/YIST, DCPL 1.1707 Euros





ST Restricted

Power & Discrete











MLPF-WB-04D3

Matched Low-Pass Filter for STM32WBA series

High RF performance in low PCB footprint

- Simpler integration
 - Impedance matching, harmonics filtering and antenna protection
- Cost effective
 - BOM reduction and reliability improvement
- Efficiency
 - · Optimizes wireless performance



Chip Scale Package on glass 6 bumps 1.00 x 1.60 x 0.63 mm

Applications

- BTLE 5.4, IEEE 802.15.4, Zigbee, Thread, Matter
- · Alarms, appliances, lighting, Door locks
- Smoke detectors, Heating/Cooling systems
- · Wearable and medical equipment,

Competition

- Discrete RF passives

ST Competitive Edge

- · Co-designed and optimized in ST by STM32 and RF IPDs design teams
- Glass substrate is less sensitive to process and temperature variation
- PCB space reduction with higher RF performance vs discrete solution



12







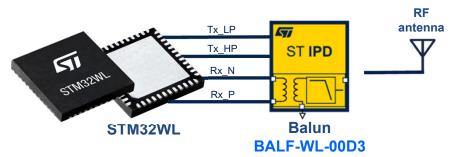
BALF-WL-00D3

868-928 MHz RF balun and filter with 2 power modes for STM32WL

Simplifying the RF complexity

- Two RF transmission paths enabling adjustable output power:
 - Low power (up to 22 dBm)
 - High power (up to 27 dBm)
- Simplify matching and filtering network complexity
 - Single chip integrates: Rx and two Tx matching networks (low power, high power), balun, harmonic filter, and ESD shunt inductor
- Bill of material reduction and 85% PCB space saving on PCB
 - Alternative to discrete solution

Reference design



Chip Scale Package on glass 15 bumps 2.40 x 2.70 x 0.63 mm

Applications

- Multiprotocol LPWAN, LoRa networks,
- Smart metering









• Industrial IoT, smart cities and buildings

Competition

- Discrete RF passives

crete RF passives

ST Competitive Edge

- Co-designed and optimized in ST by STM32 and RF IPDs design teams
- Glass substrate is less sensitive to process and temperature variation
- PCB space reduction with higher RF performance vs discrete solution









STPOWER SiC MOSFET Gen 3

GROWTH DRIVERS

Gen 2

25 mohm

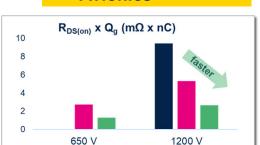
More Power

- Better efficiency
- Smaller form factor
- Lower Total Costs Ownership vs. silicon technologies
- **The Energy Transition:**
 - Silicon Carbide is the key enabling technology

High End Industrial

KEY APPLICATIONS

- **Solar Inverter**
- **Energy Storage**
- **Data centers**
- **Power Supply**
- **Charging Station**
- Welding
- **Drives**
- **Avionics**









Wide Voltage Range **650V**, **750V**, **900V**, **1200V**

RDs (on) Range from 55 m Ω to 11 m Ω

18 V driving voltage but it is suitable to be driven at Vgs 15 V

Ultrafast series optimizing Ron and Qg for very high frequency applications



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Gen 1

50 mohm





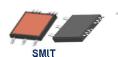








New top side cooling solutions





Die business



ST Restricted



14 mohm

1200V

Gen 3



TOLL

High Creepage**

** 1100 V_{RMS} insulation - coming soon

TO-247 3LL TO-247 4L

Commercial Product H2PAK-7 SCT012H90G3AG 28.0000 SCT015W120G3-4AG TO247-4 SCT018H65G3AG H2PAK-7 11.1000 TO247-4 SCT018W65G3-4AG 11.5000 SCT025W120G3-4AG TO247-4 11.8000 SCT027W65G3-4AG TO247-4 8.5000 SCT040H120G3AG H2PAK-7 8.5000 SCT040H65G3AG H2PAK-7 6.3500 HU3PAK - MIXED BE PLANT 7.5000 SCT040HU65G3AG SCT040W120G3-4AG 8.6000 SCT040W120G3AG HiP-247 IN LINE HEAT SINK 2MM 8 5500 SCT055HU65G3AG HU3PAK - MIXED BE PLANT 6.2409 SCT055W65G3-4AG TO247-4 6.0500 SCT060HU75G3AG HU3PAK 6.3500 SCT070H120G3AG H2PAK-7 5.7000 SCT070HU120G3AG HU3PAK - MIXED BE PLANT 6.5000 SCT070W120G3-4AG TO247-4 6.3000 HIP-247 IN LINE HEAT SINK 2MM 4.0000 SCT1000N170 SCT10N120 HiP-247 IN LINE HEAT SINK 2MM 4.5309 SCT10N120AG HiP-247 IN LINE HEAT SINK 2MM 5.1118 SCT20N120 HiP-247 IN LINE HEAT SINK 2MM 7.7440 SCT20N120AG HiP-247 IN LINE HEAT SINK 2MM 8.5970 7.3810 SCT20N120H H2PAK HC 2-3 Leads SCT30N120 HiP-247 IN LINE HEAT SINK 2MM 12.1000 SCT30N120H H2PAK HC 2-3 Leads 11.9790 HiP-247 IN LINE HEAT SINK 2MM SCT50N120 18.8206 SCTH100N65G2-7AG 17.6660 H2PAK-7 SCTH35N65G2V-7 H2PAK-7 7.2600 SCTH35N65G2V-7AG H2PAK-7 7.5600 SCTH40N120G2V-7 H2PAK-7 9.1960 SCTH40N120G2V7AG H2PAK-7 10.1073 SCTH60N120G2-7 H2PAK-7 14.6410 SCTH70N120G2V-7 H2PAK-7 23,4000 SCTH90N65G2V-7 H2PAK-7 17.3030 SCTL35N65G2V Power FLAT MLPD 8x8 4L 8.4000 SCTL90N65G2V Power FLAT MLPD 8x8 4L 18.0290 SCTW100N65G2AG HiP-247 IN LINE HEAT SINK 2MM 18.0000 SCTW35N65G2V HIP-247 IN LINE HEAT SINK 2MM 8.0000 SCTW35N65G2VAG HiP-247 IN LINE HEAT SINK 2MM 8.3000 SCTW40N120G2V 9.8010 HiP-247 IN LINE HEAT SINK 2MM SCTW40N120G2VAG HiP-247 IN LINE HEAT SINK 2MM 10.8900 SCTW60N120G2 HiP-247 IN LINE HEAT SINK 2MM 15.6090 SCTW70N120G2V 24.2000 HiP-247 IN LINE HEAT SINK 2MM SCTW90N65G2V HiP-247 IN LINE HEAT SINK 2MM 17.9080 SCTWA20N120 TO-247 LONG LEADS 8.2280 SCTWA30N120 TO-247 LONG LEADS 15.4880 SCTWA35N65G2V TO-247 LONG LEADS 8.1000 SCTWA35N65G2V-4 TO247-4 8.2000 SCTWA40N120G2V TO-247 LONG LEADS 9.8900 SCTWA40N120G2V-4 TO247-4 9.9912 SCTWA40N12G24AG TO247-4 11.0000 SCTWA50N120 TO-247 LONG LEADS 19.1691 SCTWA60N120G2-4 TO247-4 16.2100 SCTWA70N120G2V-4 TO247-4 24.6600 SCTWA90N65G2V TO-247 LONG LEADS 18.5130 SCTWA90N65G2V-4 TO247-4 18.6000

SiC MOSFET Available for Mass Market

- 56 Total Devices in Available in DCPL
- 17 Devices introduced in Q1 24 from latest Gen 3 Silicon Carbide MOSFET
- Wide Portfolio of Rds (on) and Packages....
- EPL Design Registration



Accelerating expansion of Silicon Carbide device manufacturing capacity

In volume production with SiC devices since 2017

- 1B\$ SiC MOSFET Revenue 2023 achieved
- Automotive & Industrial Market Segment

Acquisition of Norstel AB in Q4'19 (*)

- to establish internal manufacturing capacity and know-how
- First prototypes of 200mm wafers achieved
- Extended Supply Chain capability thanks to Multi-Year agreement with Cree and SiCrystal on Silicon Carbide 150mm wafers
- · Assy & Testing at two sites: Shenzhen & Bouskoura

Vertical Integration for a strategic balance: Internal & Suppliers capabilities (Sanan)











(*) Norstel AB renamed as ST SiC since 2020

Thank you

